

DESCRIPTION

2SA1287 is silicon PNP epitaxial type transistor. Designed with high Voltage, high collector current, dissipation and high h_{FE} .

Complementary with 2SC3247.

FEATURE

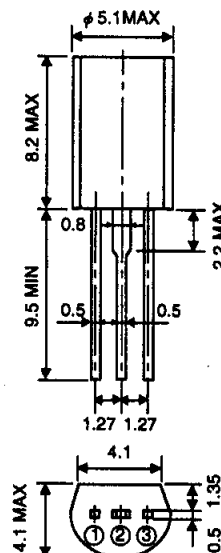
- High h_{FE} $h_{FE}=400$ to 800
- High voltage $V_{CEO}=-50V$
- Low collector to emitter saturation voltage.
 $V_{CE(sat)}=-0.2V$ ($I_C=-500mA$, $I_B=-10mA$)
- High collector dissipation $P_C=900mW$

APPLICATION

Relay drive or power supply of audio machine, VCR, and other electronic machine.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ① : EMITTER EIAJ : —
- ② : COLLECTOR JEDEC : —
- ③ : BASE

Note)
The dimension without tolerance represent central value.

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

Symbol	Parameter	Ratings	Unit
V_{CBO}	Collector to Base voltage	-50	V
V_{EBO}	Emitter to Base voltage	-6	V
V_{CEO}	Collector to Emitter voltage	-50	V
I_{CM}	Peak collector current	-2	A
I_C	Collector current	-1	A
P_C	Collector dissipation($T_a=25^{\circ}C$)	900	mW
T_j	Junction temperature	+150	$^{\circ}C$
T_{stg}	Storage temperature	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

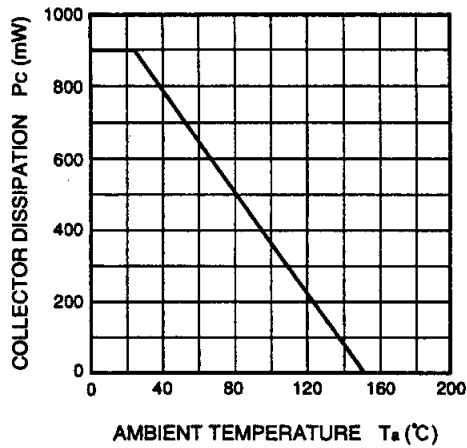
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C=-10\mu A, I_E=0$	-50			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=-10\mu A, I_C=0$	-6			V
$V_{(BR)CEO}$	C to E break down voltage	$I_C=-1mA, R_{BE}=\infty$	-50			V
I_{CBO}	Collector cut off current	$V_{CB}=-40V, I_E=0$			-0.1	μA
I_{EBO}	Emitter cut off current	$V_{EB}=-2V, I_C=0$			-0.1	μA
h_{FE}^*	DC forward current gain	$V_{CE}=-6V, I_C=-100mA$	400		800	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=-500mA, I_B=-10mA$		-0.2	-0.5	V
f_T	Gain band width product	$V_{CE}=-10V, I_E=10mA$		90		MHz
C_{ob}	Collector output capacitance	$V_{CB}=-10V, I_E=0, f=1MHz$		30		pF

* : It shows h_{FE} classification in right table.

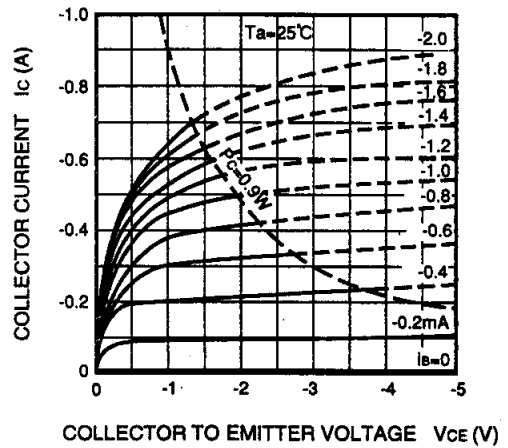
Item	G
h_{FE}	400 to 800

TYPICAL CHARACTERISTICS

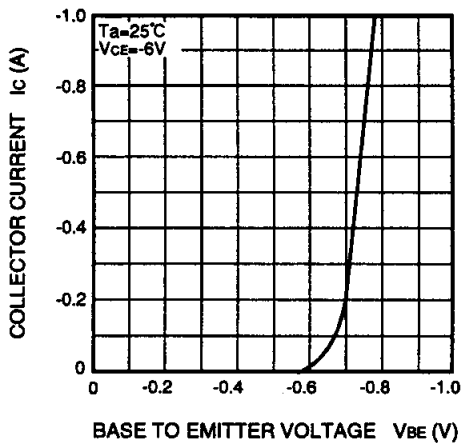
**COLLECTOR DISSIPATION VS.
AMBIENT TEMPERATURE**



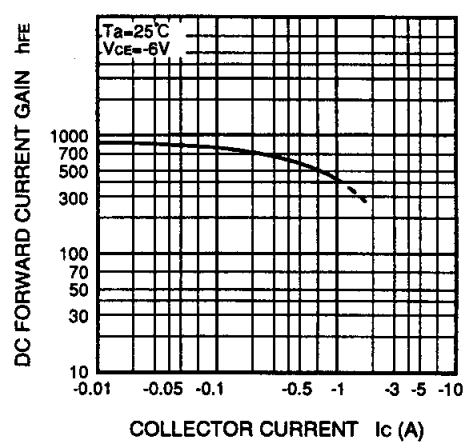
COMMON EMITTER OUTPUT



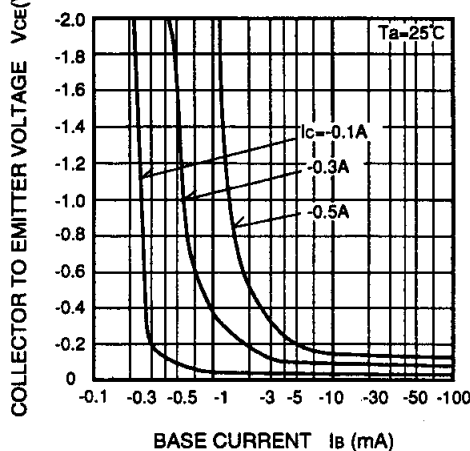
COMMON EMITTER TRANSFER



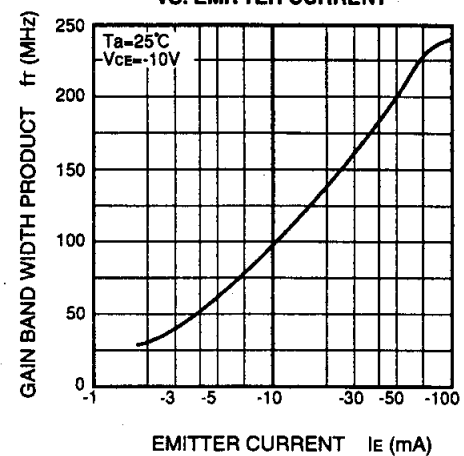
**DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT**



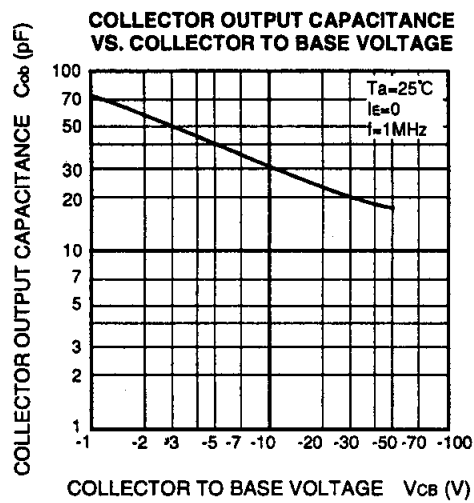
**COLLECTOR TO EMITTER SATURATION
VOLTAGE VS. BASE CURRENT**



**GAIN BAND WIDTH PRODUCT
VS. EMITTER CURRENT**



FOR RELAY DRIVE, POWER SUPPLY APPLICATION
SILICON PNP EPITAXIAL TYPE





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